

MOTOROLA
SEMICONDUCTOR
 TECHNICAL DATA

 T-11-11
1N3016 thru 1N3051
 See Page 4-32

1N3154,A
 thru
1N3157,A
TEMPERATURE-COMPENSATED SILICON
ZENER REFERENCE DIODES

Temperature-compensated zener reference diodes utilizing an oxide-passivated junction for long-term voltage stability. A rugged, glass-enclosed, hermetically sealed structure.

TEMPERATURE-COMPENSATED
SILICON ZENER
REFERENCE DIODES
 8.4 V, 500 mW

MAXIMUM RATINGS

Junction Temperature: -55 to +175°C
 Storage Temperature: -65 to +175°C
 DC Power Dissipation: 500 mW @ $T_A = 25^\circ\text{C}$

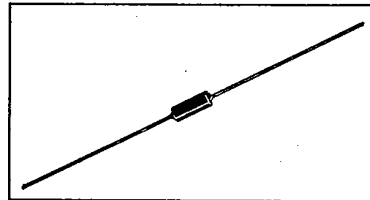
MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, all glass.
DIMENSIONS: See outline drawing.
FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
POLARITY: Cathode indicated by polarity band.
WEIGHT: 0.2 Grams (approx)
MOUNTING POSITION: Any

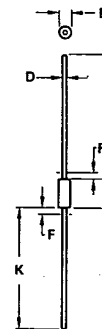
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)
 $V_Z = 8.4\text{ V} \pm 5.0\% @ I_{ZT} = 10\text{ mA}$

JEDEC Type No. (Note 1)	Maximum Voltage Change ΔV_Z (Volts) (Note 2)	Ambient Test Temperature $^\circ\text{C}$ $\pm 1^\circ\text{C}$	Temperature Coefficient %/ $^\circ\text{C}$ (Note 2)	Maximum Dynamic Impedance Z_{ZT} (Ohms) (Note 3)
1N3154	0.130	-55, 0, +25, +75, +100	0.01	15
1N3155	0.065		0.005	
1N3156	0.026		0.002	
1N3157	0.013		0.001	
1N3154A	0.172	-55, 0, +25, +75, +100, +150	0.01	15
1N3155A	0.086		0.005	
1N3156A	0.034		0.002	
1N3157A	0.017		0.001	

*Tighter-tolerance units available on special request.
 CAPACITANCE (C) = 20 to 180 pF @ 90% of V_Z
 FORWARD BREAKDOWN VOLTAGE (V_F) = 100 to 800 V



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DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	-	1.27	-	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS
NOTES:

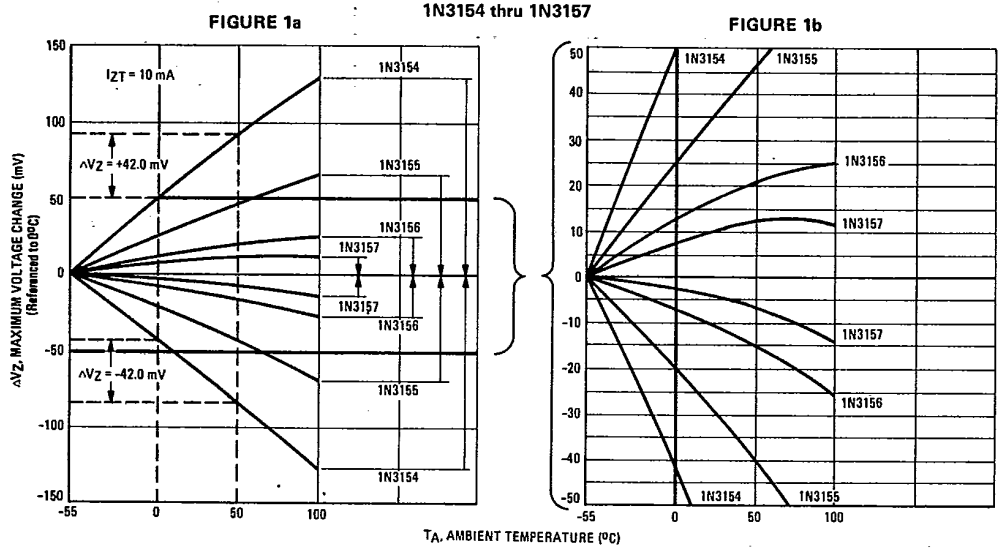
- PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
- LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

1N3154A thru 1N3157A

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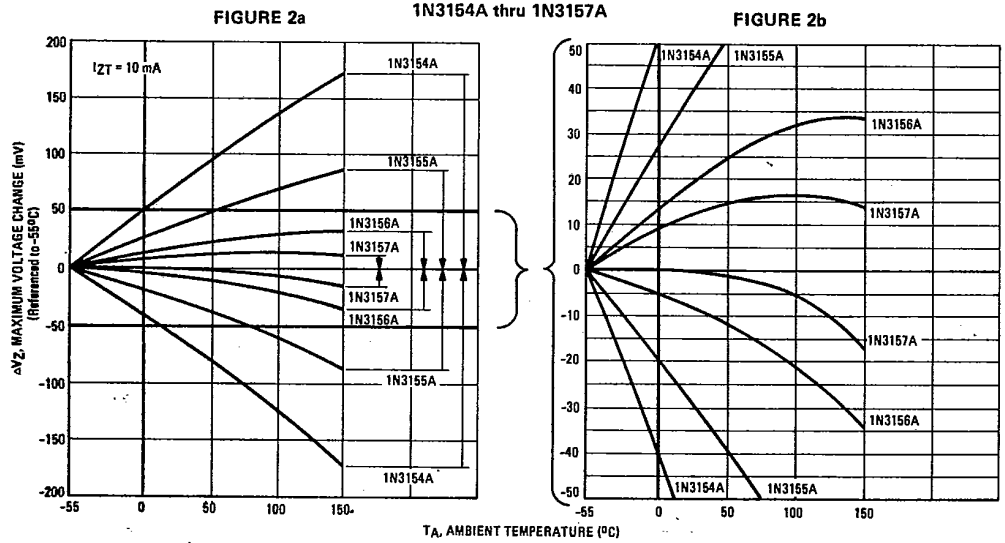
MAXIMUM VOLTAGE CHANGE versus AMBIENT TEMPERATURE

(with $I_{ZT} = 10 \text{ mA} \pm 0.01 \text{ mA}$) (See Note 4)



MAXIMUM VOLTAGE CHANGE versus AMBIENT TEMPERATURE

(with $I_{ZT} = 10 \text{ mA} \pm 0.01 \text{ mA}$) (See Note 4)



1N3154A thru 1N3157A

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FIGURE 3 — ZENER CURRENT versus MAXIMUM VOLTAGE CHANGE (at specified temperatures)
(See Note 5)

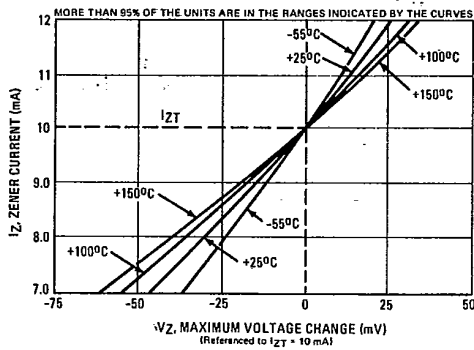


FIGURE 4 — MAXIMUM ZENER IMPEDANCE versus ZENER CURRENT
(See Note 3)

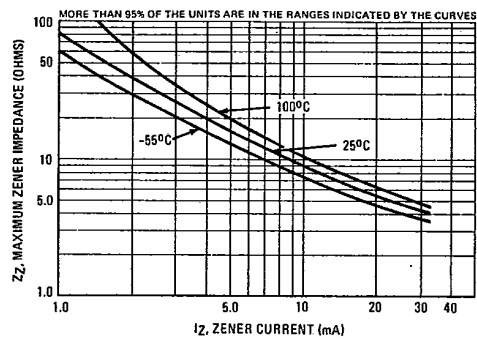
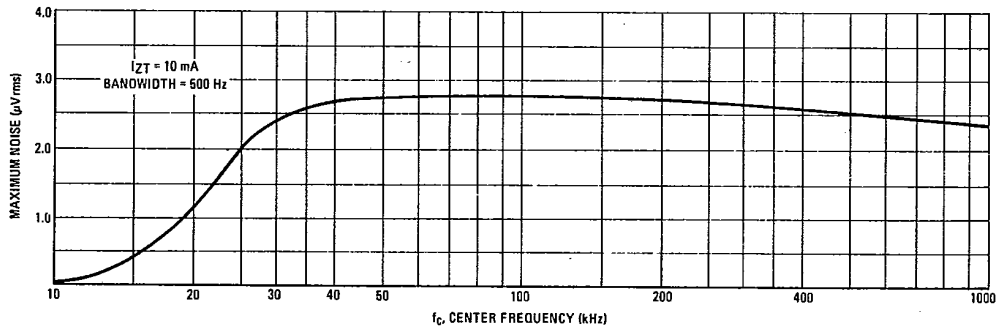


FIGURE 5 — DISTRIBUTION OF MAXIMUM GENERATED NOISE

**NOTE 1:**

Types 1N3154 thru 1N3157 are available to MIL-S-19500/158 and MEG-A-LIFE II, Levels 1, 2, & 3, specifications.

NOTE 2:

Voltage Variation (ΔV_Z) and Temperature Coefficient.

All reference diodes are characterized by the "box method". This guarantees a maximum voltage variation (ΔV_Z) over the specified temperature range, at the specified test current (I_{ZT}), verified by tests at indicated temperature points within the range. This method of indicating voltage stability is now used for JEDEC registration as well as for military qualification. The former method of indicating voltage stability — by means of temperature coefficient — accurately reflects the voltage deviation at the temperature extremes, but is not necessarily accurate within the temperature range because reference diodes have a nonlinear temperature relationship. The temperature coefficient, therefore, is given only as a reference.

NOTE 3:

Zener Impedance Derivation

The dynamic zener impedance, Z_{ZT} , is derived from the 60-Hz ac voltage drop which results when an ac current with an rms value equal to 10% of the dc zener current, I_{ZT} , is superimposed on I_{ZT} .

Curves showing the variation of zener impedance with zener current for each series are given in Figure 4. A cathode-ray tube curve-trace test on a sample basis is used to ensure that each zener characteristic has a sharp and stable knee region.

NOTE 4:

These graphs can be used to determine the maximum voltage change of any device in the series over any specific temperature range. For example, a temperature change from 0 to +50°C will cause a voltage change no greater than +42 mV or -42 mV for 1N3154, as illustrated by the dashed lines in Figure 1. The boundaries given are maximum values. For greater resolution, expanded views of the shaded areas in Figures 1a and 2a are shown in Figures 1b and 2b respectively.

NOTE 5:

The maximum voltage change, ΔV_Z , in Figure 3 is due entirely to the impedance of the device. If both temperature and I_{ZT} are varied, then the total voltage change may be obtained by adding ΔV_Z in Figure 3 to the ΔV_Z in Figure 1 or 2 for the device under consideration. If the device is to be operated at some stable current other than the specified test current, a new set of characteristics may be plotted by superimposing the data in Figure 3 on Figure 1 or 2.